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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/852,647	05/11/2001	Sahng-ik Jun	06192.0178.NPUS00	5231
75	590 06/28/2004		EXAMINER	
McGuireWoods LLP			DUONG, THOI V	
1750 Tysons Boulevard Suite 1800			ART UNIT	PAPER NUMBER
McLean, VA 22102-4215			2871	
			DATE MAILED: 06/28/200-	4

Please find below and/or attached an Office communication concerning this application or proceeding.

•	Application No.	Applicant(s)					
	09/852,647	JUN, SAHNG-IK	JUN, SAHNG-IK				
Office Action Summary	Examiner	Art Unit	ليم				
	Thoi V Duong	2871	P				
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet w	vith the correspondence add	iress				
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period of Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a y within the statutory minimum of thi will apply and will expire SIX (6) MO , cause the application to become A	reply be timely filed  rty (30) days will be considered timely.  NTHS from the mailing date of this cor.  BANDONED (35 U.S.C. § 133).	mmunication.				
Status							
1) Responsive to communication(s) filed on 14 A	<u>oril 2004</u> .						
2a)⊠ This action is <b>FINAL</b> . 2b)☐ This	This action is <b>FINAL</b> . 2b) This action is non-final.						
3) Since this application is in condition for alloward	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.							
Disposition of Claims							
4)⊠ Claim(s) <u>1-38</u> is are pending in the application.							
4a) Of the above claim(s) is/are withdrawn from consideration.							
5)⊠ Claim(s) <u>10-34</u> is/are allowed.							
6)⊠ Claim(s) <u>1-9 and 35-38</u> is/are rejected.							
7) Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction and/or election requirement.							
Application Papers							
9)☐ The specification is objected to by the Examiner.							
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.							
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).							
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).							
11) ☐ The oath or declaration is objected to by the Ex	caminer. Note the attache	ed Office Action or form PTC	O-152. `				
Priority under 35 U.S.C. § 119							
<ul> <li>12) Acknowledgment is made of a claim for foreign</li> <li>a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority document</li> </ul>		§ 119(a)-(d) or (f).					
<ul> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No</li> </ul>							
3. Copies of the certified copies of the priority documents have been received in this National Stage							
application from the International Bureau	•		J				
* See the attached detailed Office action for a list	of the certified copies no	t received.					
Attachment(s)							
1) Notice of References Cited (PTO-892)	4) Interview	Summary (PTO-413)					
2) D Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No	(s)/Mail Date Informal Patent Application (PTO-	152)				
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	6) Other:	• • • • • • • • • • • • • • • • • • • •	-152)				

#### **DETAILED ACTION**

1. This office action is in response to the Amendment filed April 14, 2004.

Accordingly, claims 1 and 35-38 were amended. Currently, claims 1-38 are pending in this application.

#### Response to Arguments

2. Applicant's arguments with respect to claims 1-9 and 35-38 have been considered but are moot in view of the new ground(s) of rejection.

## Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical Amendments Act of 2002 do not apply when the reference is a U.S. patent resulting directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

4. Claims 1-6, 8, 9 and 35-38 are rejected under 35 U.S.C. 102(e) as being anticipated by Fukuda (USPN 6,746,905 B1).

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Re claim 1, as shown in Figs. 4A and 4B, Fukuda discloses a liquid crystal display, comprising:

a plurality of gate lines 42 formed on a substrate 11;

a plurality of data lines 41 insulated from and crossing over said plurality of gate lines;

a plurality of pixel regions defined by the crossing of said plurality of gate lines and said plurality of data lines (Fig. 4A);

a semiconductor layer comprising a semiconductor pattern 12 and a light interception pattern 63 as shown in Fig. 9 (col. 5, lines 37-41 and col. 13, lines 24-35); and

a thin film transistor provided to each pixel region and including the semiconductor pattern,

wherein, re claim 2, as shown in Fig. 4B, said light interception pattern included in the semiconductor film and said data line 41 corresponding thereto overlap each other, and said light interception pattern and said pixel electrode 32 close to said data line corresponding thereto overlap each other;

wherein, re claim 4, the semiconductor pattern 12 is connected to said light interception pattern corresponding thereto (col. 13, lines 36-43);

wherein, re claim 5, the semiconductor pattern is extended to said data line corresponding thereto (Fig. 4B);

wherein, re claim 6, the light interception pattern 63 is extended beyond a periphery of said data line corresponding thereto (Fig. 4A); and

wherein, re claim 8, said pixel electrode 32 is formed on the same plane as said plurality of data lines 41 (Fig. 4B).

As shown in Fig. 10, Fukuda further discloses a common electrode 75 formed in each pixel region; and

a pixel electrode 22 formed in each pixel region, spaced apart from said common electrode with a predetermined distance therebetween (as thickness of liquid crystal layer 73),

wherein, re claim 9, said pixel electrode is formed on the plane different from said plurality of data lines; and

wherein, re claim 3, said light interception pattern 63 and a common electrode 75 overlap each other since the light interception pattern 63 overlaps the thin film transistor.

Re claim 35, as shown in Figs. 4A and 4B, Fukuda discloses a liquid crystal display, comprising:

- a gate line 42 formed on a substrate 11;
- a data line 41 insulated from and intersecting said gate line;
- a semiconductor layer comprising a semiconductor pattern 12 and a light interception pattern 62 as shown in Fig. 9 (col. 5, lines 37-41 and col. 13, lines 24-35);
- a thin film transistor connected to said gate line and said data line, said thin film transistor including the semiconductor pattern; and
- a field-generating electrode 32 having a portion laterally spaced apart from said data line with a gap therebetween,

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wherein the semiconductor layer comprising the light interception pattern overlaps the gap (Fig. 4B);

wherein, re claim 36, said light interception pattern and said data line overlap each other, and said light interception pattern and said field-generating electrode overlap each other (Fig. 4B);

wherein, re claim 37, the semiconductor layer is connected to said light interception pattern (col. 13, lines 36-43); and

wherein, re claim 38, said light interception pattern included in the semiconductor film is wider than said data line 41 (Fig. 4A).

#### Claim Rejections - 35 USC § 103

- 5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. Claim 7 is rejected under 35 U.S.C. 103(a) as being unpatentable over Fukuda (USPN 6,746,905 B1) in view of Yamazaki et al. (USPN 5,892,562).

Fukuda discloses a liquid crystal display device that is basically the same as that recited in claim 7 except for a common electrode formed on the same plane as said plurality of gate lines.

As shown in Figs. 4 and 5, Yamazaki et al. discloses a common electrode 404 in formed on the same plane as a plurality of gate lines 403 (col. 5, lines 5-9). Similarly, in

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Figs. 6 and 7A, Yamazaki et al. also discloses a common electrode 609 formed on the same plane as a plurality of gate lines 608.

Thus, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the liquid crystal display of Fukuda with the teaching of Yamazaki et al. by having a common electrode formed on the same plane as said plurality of gate lines so as to control the strength of an electric field (a horizontal electric field) between a drain electrode and a common electrode (col. 5, lines 11-15).

#### Allowable Subject Matter

### 7. Claims 10-34 are allowed.

The following is an examiner's statement of reasons for allowance: none of the prior art of record fairly suggests or shows all of the limitations as claimed. Specifically,

Re claims 10 and 22, none of the prior art of record discloses, in combination with other limitations as claimed, a liquid crystal display (as well as a method of fabricating the same) comprising a light interception pattern formed of the same material as said semiconductor pattern on the gate insulating layer.

The most relevant references, USPN 6,466,289 B1 of Lee et al. and USPN 5,247,289 of Matsueda, fail to disclose or suggest a semiconductor layer comprising a semiconductor pattern and a light interception pattern or a light interception pattern formed of the same material as said semiconductor pattern on the gate insulating layer. As shown in Figs. 3, 6 and 7, the reference of Lee et al. discloses a light interception pattern 64 and a semiconductor pattern 40 formed on the gate insulating layer 30;

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however, the material of the light interception pattern 64 is different from that of the semiconductor pattern 40 (col. 3, lines 33-34 and 54-56). Meanwhile, as shown in Fig. 7, the Matsueda's reference discloses a semiconductor portion formed of the same layer as a semiconductor pattern 78 on top of a common electrode 81; however, this semiconductor portion does not function as a light interception pattern.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

#### Conclusion

8. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

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9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thoi V. Duong whose telephone number is (571) 272-2292. The examiner can normally be reached on Monday-Friday from 8:30 am to 4:30 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Robert Kim, can be reached at (571) 272-2293.

Thoi Duong

06/18/2004

ROBERT (H. KIM

SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800